

General Description

These Power MOSFETs are produced using Cmos's proprietary, planar stripe, DMOS technology. These devices are well suited for electronic lamp ballast based on complementary half bridge.

Features

- Low On-Resistance
- 100% avalanche tested
- Simple Drive Requirement
- RoHS Compliant

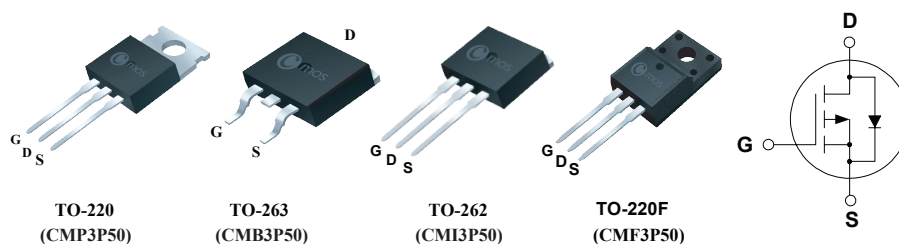
Product Summary

BVDSS	R _{DS(on)} max.	ID
-500V	14Ω	-2A

Applications

- DC-DC Converters
- Power Management Functions

TO-220/263/262/220F Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	220/263/262	220F	Units
V _{DS}	Drain-Source Voltage	-500		V
V _{GS}	Gate-Source Voltage	±20		V
I _D @T _C =25°C	Continuous Drain Current	-2	-2*	A
I _D @T _C =100°C	Continuous Drain Current	-1.3	-1.3*	A
I _{DM}	Pulsed Drain Current	-8	-8*	A
EAS	Single Pulse Avalanche Energy (Note 1)	135		mJ
P _D @T _C =25°C	Total Power Dissipation	65	30	W
T _{STG}	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150		°C

* Drain current limited by maximum junction temperature.

Thermal Data

Symbol	Parameter	220/263/262	220F	Unit
R _{θJA}	Thermal Resistance Junction-ambient Max.	62.5	62.5	°C/W
R _{θJC}	Thermal Resistance Junction-case Max.	1.92	4.17	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-500	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V$, $I_D=-2A$	---	12.5	14	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-2	---	-4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-500V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	-1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-15V$, $I_D=-1A$	---	1.9	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3.0	---	Ω
Q_g	Total Gate Charge	$V_{DS}=-400V$, $I_D=-1.5A$ $V_{GS}=-10V$	---	11	---	nC
Q_{gs}	Gate-Source Charge		---	2	---	
Q_{gd}	Gate-Drain Charge		---	5.6	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=-250V$, $R_L=25\Omega$ $I_D=-1.5A$	---	9	---	ns
T_r	Rise Time		---	25	---	
$T_{d(off)}$	Turn-Off Delay Time		---	27	---	
T_f	Fall Time		---	30	---	
C_{iss}	Input Capacitance	$V_{DS}=-25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	330	---	pF
C_{oss}	Output Capacitance		---	26	---	
C_{rss}	Reverse Transfer Capacitance		---	5	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-2	A
I_{SM}	Pulsed Source Current		---	---	-8	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_F=-3A$	---	---	-5	V

Note :

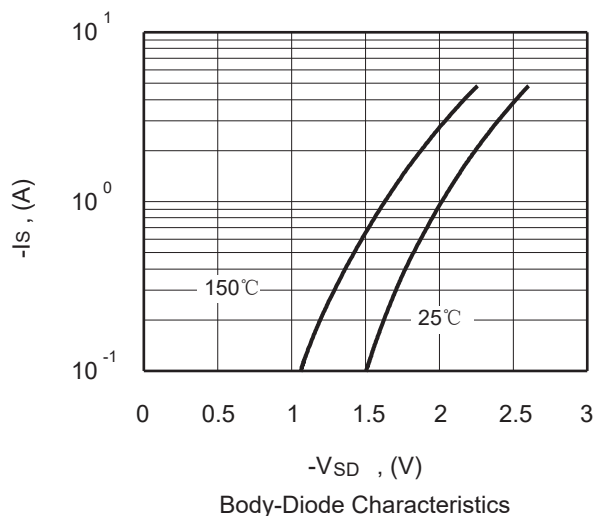
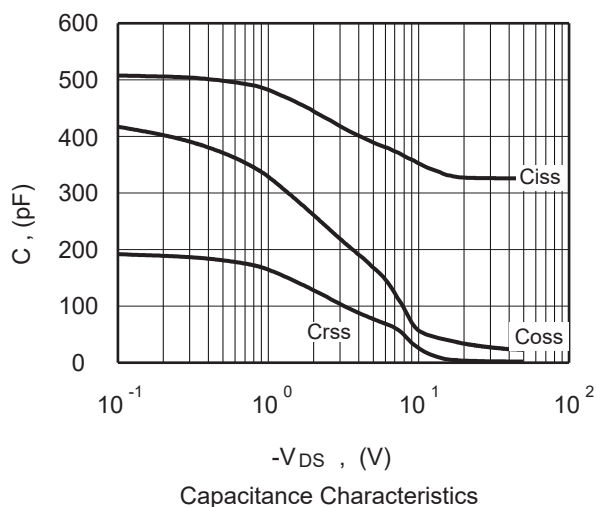
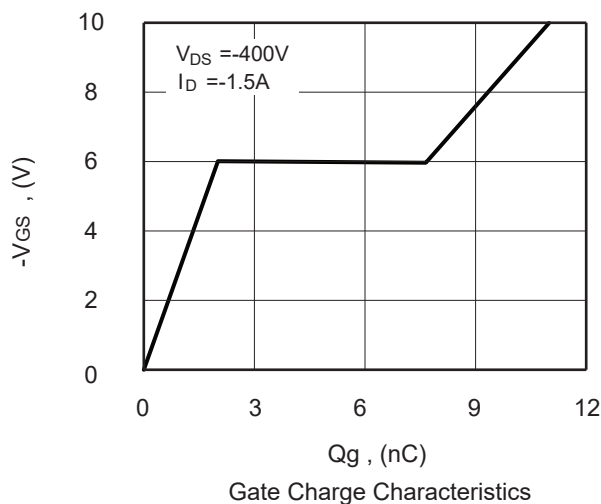
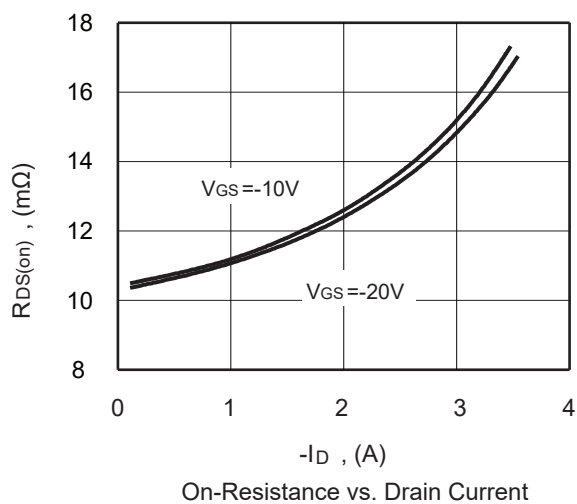
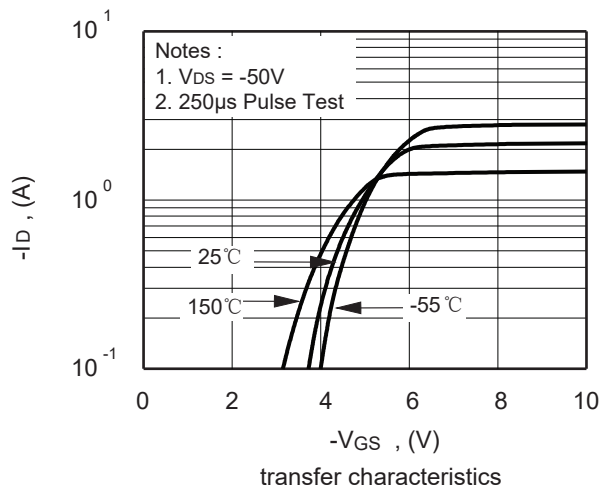
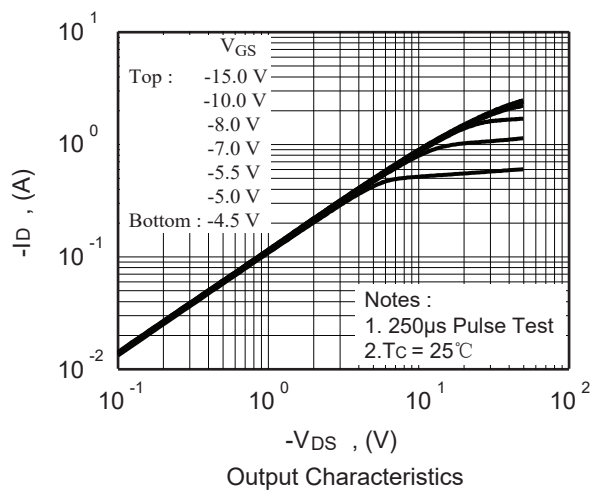
1.The EAS data shows Max. rating .The test condition is $V_{DS}=-100V$, $V_{GS}=-10V$, $L=30\text{mH}$, $I_{AS}=-3A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

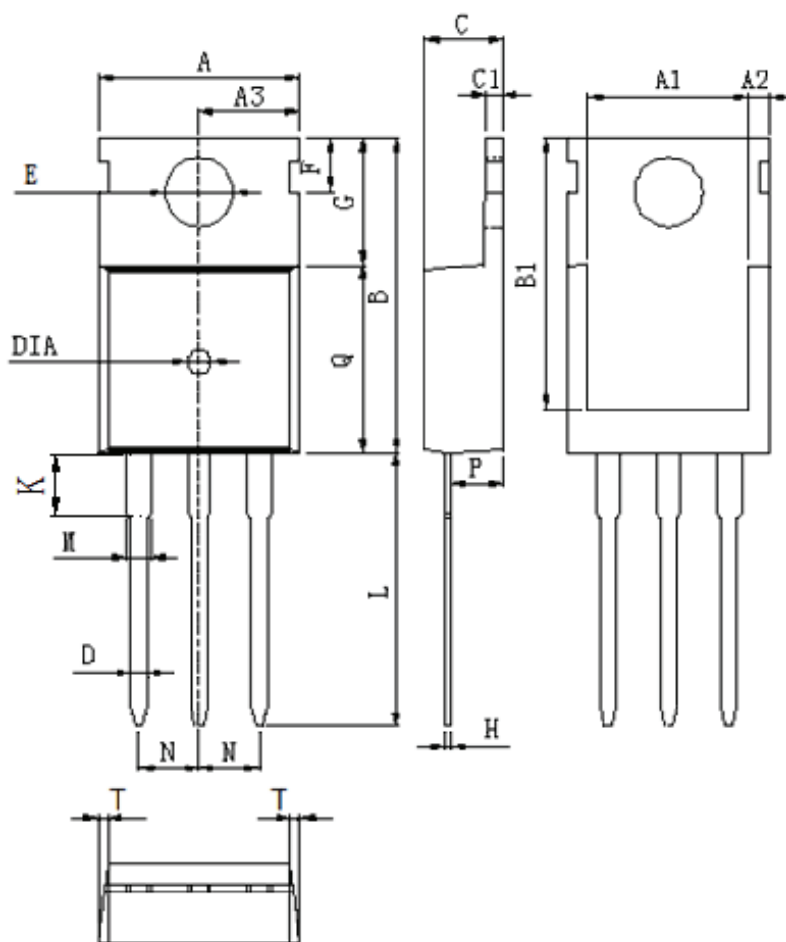
Typical Characteristics



Package Dimension

TO-220

Unit :mm

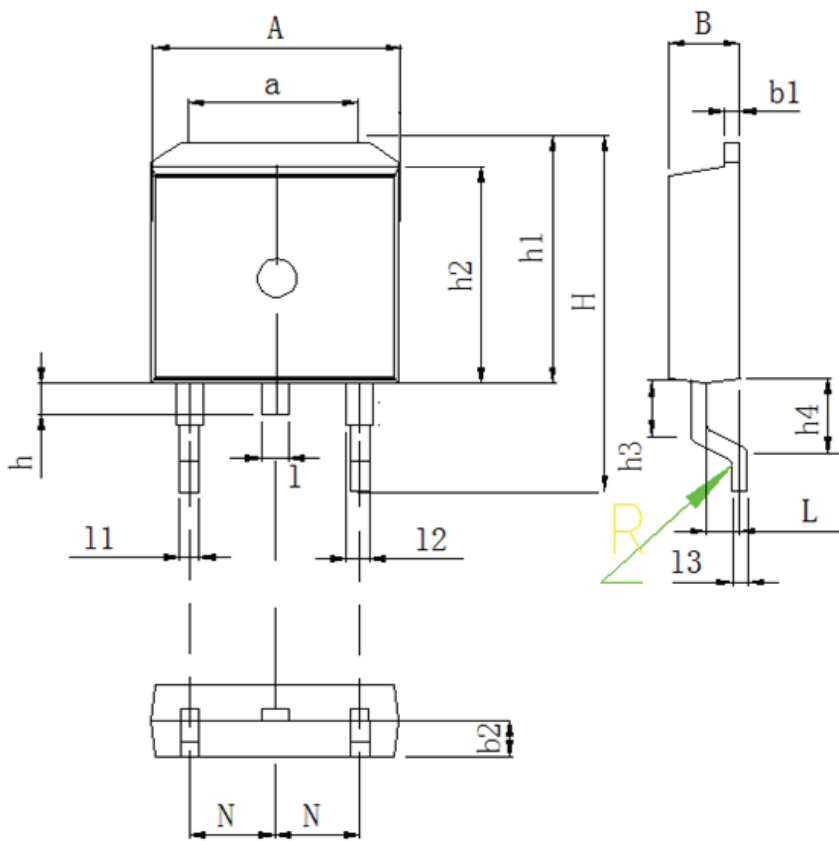


DIM	MILLIMETERS
A	10.0 ± 0.3
A1	8.64 ± 0.2
A2	1.15 ± 0.1
A3	5.0 ± 0.2
B	15.8 ± 0.4
B1	13.2 ± 0.3
C	4.56 ± 0.1
C1	1.3 ± 0.2
D	0.8 ± 0.2
E	3.6 ± 0.2
F	2.95 ± 0.3
G	6.5 ± 0.3
H	0.5 ± 0.1
K	3.1 ± 0.2
L	13.2 ± 0.4
M	1.25 ± 0.1
N	2.54 ± 0.1
P	2.4 ± 0.3
Q	9.0 ± 0.3
T	W:0.35
DIA	$\odot 1.5$ (deep 0.2)

Package Dimension

TO-263

Unit :mm

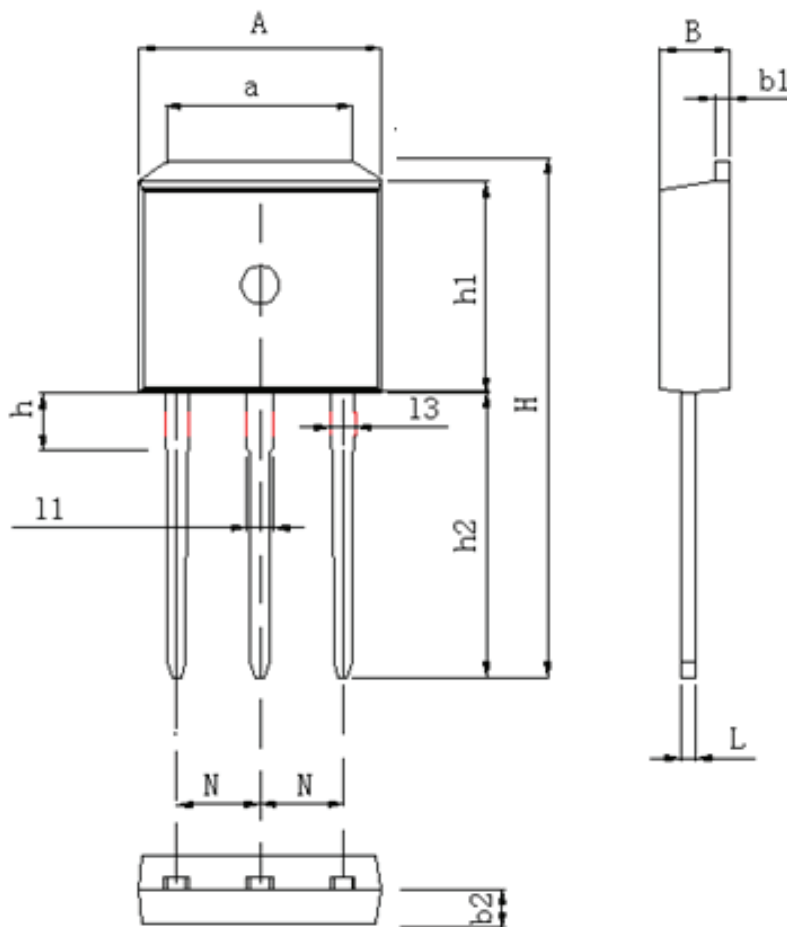


DIM	MILLIMETERS
A	9.8±0.2
a	7.4±0.4
B	4.5±0.2
b1	1.3±0.05
b2	2.4±0.2
H	15.5±0.3
h	1.54±0.2
h1	10.5±0.2
h2	9.2±0.1
h3	1.54±0.2
h4	2.7±0.2
L	2.4±0.2
1	1.3±0.1
11	0.8±0.1
12	1.3±0.1
13	0.5±0.1
N	2.54±0.1
R	0.5R±0.05

Package Dimension

TO-262

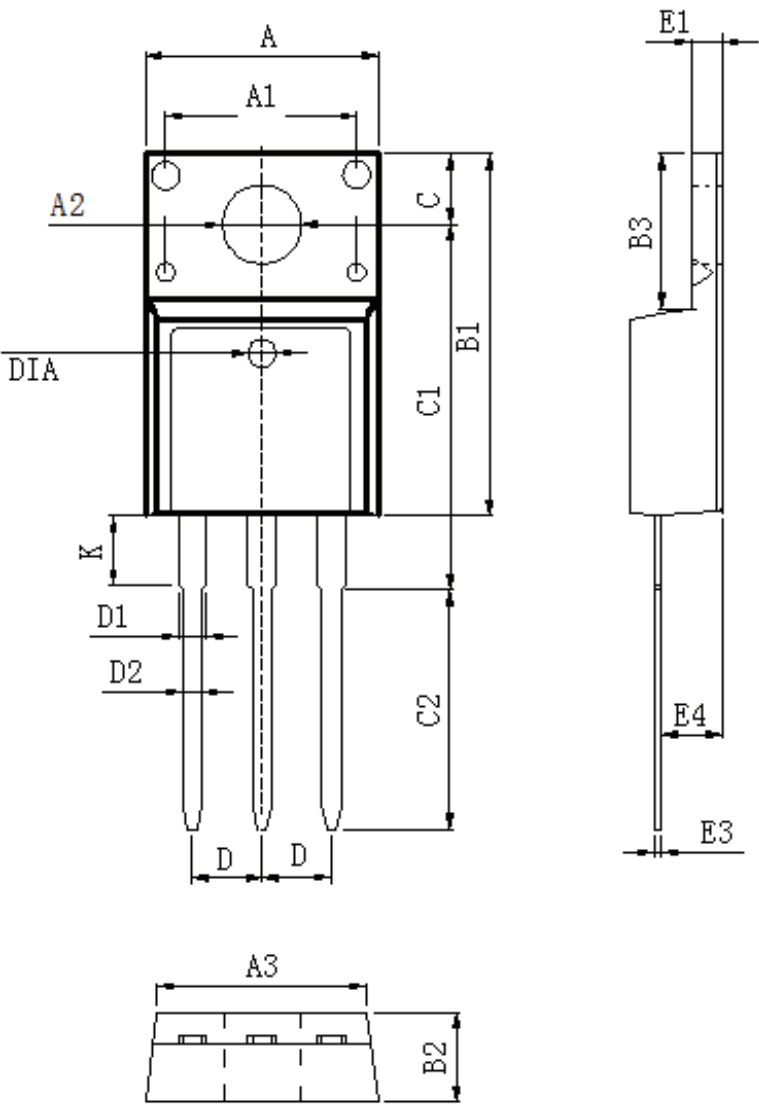
Unit :mm



DIM	MILLIMETERS
A	9.98 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	23.9 ± 0.3
h	3.1 ± 0.2
h1	9.16 ± 0.2
h2	13.2 ± 0.2
L	0.5 ± 0.1
l1	1.3 ± 0.1
l2	0.8 ± 0.1
N	2.45 ± 0.1

Package Dimension

TO-220F Unit :mm



DIM	MILLIMETERS
A	10.16±0.3
A1	7.00±0.1
A2	3.3±0.2
A3	9.5±0.2
B1	15.87±0.3
B2	4.7±0.2
B3	6.68±0.4
C	3.3±0.2
C1	12.57±0.3
C2	10.02±0.5
D	2.54±0.05
D1	1.28±0.2
D2	0.8±0.1
K	3.1±0.3
E1	2.54±0.1
E3	0.5±0.1
E4	2.76±0.2
DIA	⌀1.5 (deep 0.2)